

MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK8P60W5

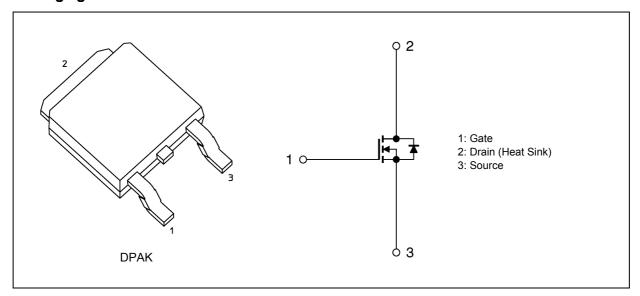
1. Applications

- Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) Fast reverse recovery time: $t_{rr} = 80 \text{ ns (typ.)}$
- (2) Low drain-source on-resistance: $R_{DS(ON)}$ = 0.44 Ω (typ.) by used to Super Junction Structure: DTMOS
- (3) Easy to control Gate switching
- (4) Enhancement mode: V_{th} = 3 to 4.5 V (V_{DS} = 10 V, I_{D} = 0.4 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	600	V
Gate-source voltage		V_{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	8.0	Α
Drain current (pulsed)	(Note 1)	I _{DP}	32	
Power dissipation $(T_c = 25^\circ)$	°C)	P_{D}	80	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	105	mJ
Avalanche current		I _{AR}	2.0	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	8.0	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	32	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	1.57	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 46.0 mH, R_G = 25 Ω , I_{AR} = 2.0 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_		±1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 0.4 mA	3	_	4.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 4.0 A		0.44	0.56	Ω

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz	_	590		pF
Reverse transfer capacitance	C_{rss}		_	1.7		
Output capacitance	C _{oss}		_	16		
Effective output capacitance	C _{o(er)}	V _{DS} = 0 to 400 V, V _{GS} = 0 V	_	33	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	7.5	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	40		ns
Switching time (turn-on time)	t _{on}		_	60	_	
Switching time (fall time)	t _f		_	5.5		
Switching time (turn-off time)	t _{off}		_	70	_	
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 4.0 A	50	_	_	V/ns

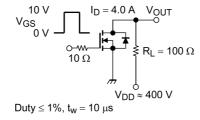


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8.0 \text{ A}$	_	22		nC
Gate-source charge 1	Q _{gs1}		_	7.5		
Gate-drain charge	Q_{gd}		_	13	_	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 8.0 A, V _{GS} = 0 V	-	1	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 4.0 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs		80	128	ns
Reverse recovery charge	Q_{rr}			0.35		μС
Peak reverse recovery current	I _{rr}		_	9.2	_	Α
Diode dv/dt ruggedness	dv/dt	I _{DR} = 4.0 A, V _{GS} = 0 V, V _{DD} = 400 V	50		_	V/ns



7. Marking

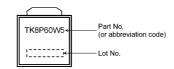


Fig. 7.1 Marking

8. Characteristics Curves (Note)

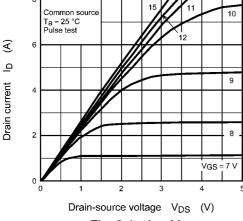
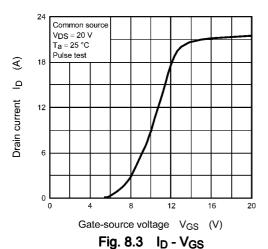


Fig. 8.1 I_D - V_{DS}



Common source VGS = 0 V ID = 10 mA Pulse test

 \Im

SSQV 650

 $\label{eq:model} \begin{array}{ll} \mbox{Ambient temperature} & \mbox{T_a} & (^{\circ}\mbox{C}) \\ \mbox{Fig. 8.5} & \mbox{V_{DSS}} - \mbox{T_a} \end{array}$

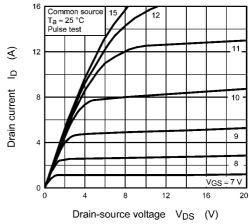
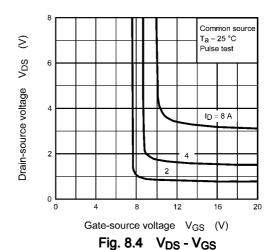


Fig. 8.2 I_D - V_{DS}



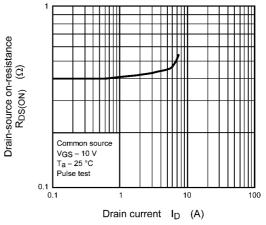


Fig. 8.6 R_{DS(ON)} - I_D

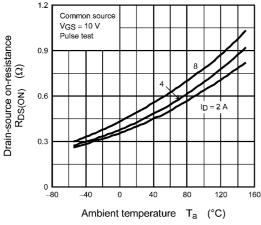


Fig. 8.7 R_{DS(ON)} - T_a

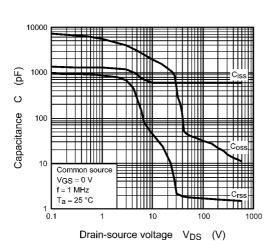


Fig. 8.9 C - V_{DS}

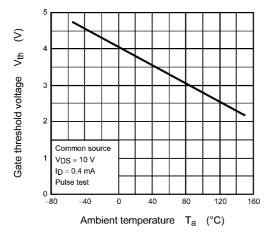


Fig. 8.11 V_{th} - T_a

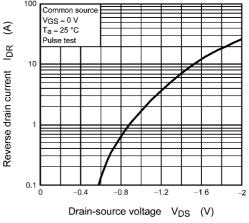


Fig. 8.8 IDR - VDS

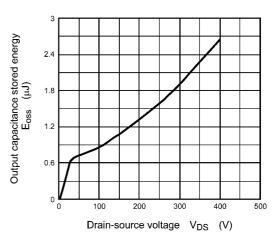


Fig. 8.10 E_{OSS} - V_{DS}

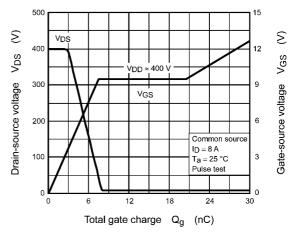


Fig. 8.12 Dynamic Input/Output Characteristics

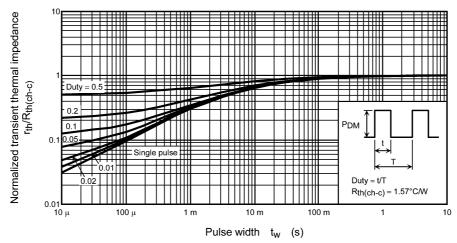


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

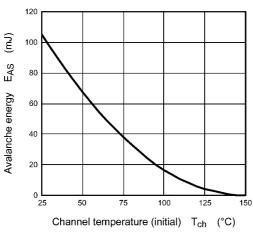


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

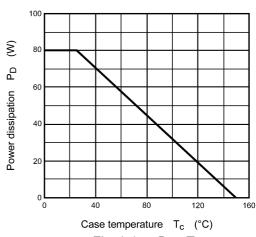


Fig. 8.15 $P_D - T_c$ (Guaranteed Maximum)

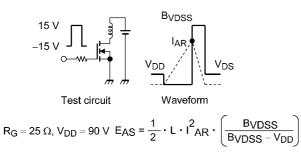


Fig. 8.16 Test Circuit/Waveform

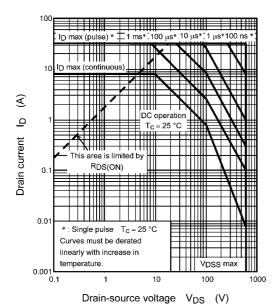


Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

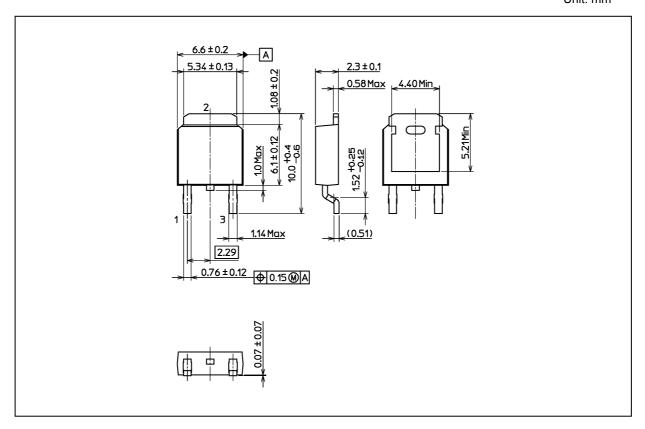
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TK8P60W5



Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

Package Name(s)
TOSHIBA: 2-7K1S
Nickname: DPAK

Rev.6.0



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